Unitized Semiconductor Devices - Page 1 of 1



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Inclosure Material:	
Metal	
Overall Length:	
0.260 inches	
Terminal Length:	
0.500 inches	
Overall Diameter:	
0.370 inches	
Joint Electronic Device Engineering Council/jedec/case Outline Designation:	
То-5	
Component Name And Quantity:	
2 transistor	
Mounting Method:	
Terminal	
Terminal Circle Diameter:	
0.200 inches	
Features Provided:	
Hermetically sealed case	
Semiconductor Material:	
Silicon all transistor	
Voltage Rating In Volts Per Characteristic:	
40.0 breakdown voltage, collector-to-base, emitter open all transistor and -40.0 breakdown voltage, collector-to-	emitter, base open all
ransistor and -5.0 breakdown voltage, emitter-to-base, collector open all transistor	
Current Rating Per Characteristic:	
60.00 milliamperes source cutoff current all transistor	
Power Rating Per Characteristic:	
70.0 milliwatts small-signal input power, common-collector preset all transistor	
Transfer Ratio:	
00.0 static forward current transfer ratio, common-emitter all transistor	
Aximum Operating Tempurature Per Measurement Point:	
200.0 degrees celsius junction	
Special Features:	
All transistor junction pattern arrangement: pnp	
Terminal Type And Quantity:	
6 uninsulated wire lead	
Shelf Life:	
N/a	
Unit Of Measure:	
Demilitarization:	
No	
Fiig:	
A110a0	